ABSTRACT

POLISHING COMPOSITION AND POLISHING METHOD

A polishing composition contains a surface irregularity-inhibitor, silicon dioxide, an acid, an oxidant, and water. The surface irregularity-inhibitor is at least one selected from, for example, stored polysaccharides and extracellular polysaccharides. The silicon dioxide is, for example, colloidal silica, fumed silica, or precipitated silica. The acid is at least one selected from, for example, nitric acid, hydrochloric acid, sulfuric acid, lactic acid, acetic acid, oxalic acid, citric acid, malic acid, succinic acid, butyric acid, and malonic acid. The oxidant is, for example, hydrogen peroxide, persulfate, periodate, perchlorate, nitrate salt, or an oxidative metallic salt. The polishing composition can be suitably used in polishing for forming wiring in a semiconductor device.

Fig. 1

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